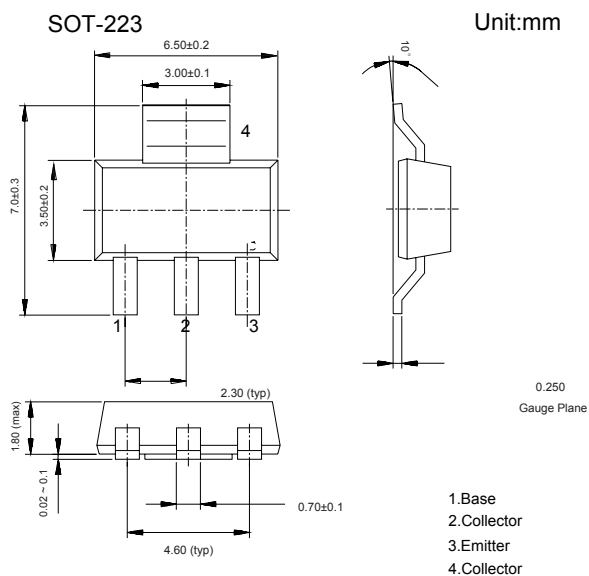
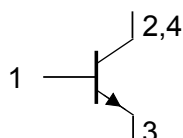


■ Features

- High current (max. 1 A)
- Low voltage (max. 20 V)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	32	V
Collector - Emitter Voltage	V _{CEO}	20	
Emitter - Base Voltage	V _{EBO}	5	
Collector Current - Continuous	I _C	1	A
Collector Current - Pulse	I _{CP}	2	
Base Current - Pulse	I _{BP}	0.2	
Collector Power Dissipation	P _C	1.37	W
Thermal Resistance from Junction to Ambient	R _{θJA}	91	°C/W
Thermal Resistance from Junction to Soldering Point	R _{θJS}	10	
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-65 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E =0	32			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = 1 mA, I _B =0	20			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _C =0	5			
Collector-base cut-off current	I _{CBO}	V _{CB} = 25 V, I _E =0			100	nA
		V _{CB} = 25 V, I _E =0, T _J =150°C			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			100	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1 A, I _B =100mA			0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =1 A, I _B =100mA			1.2	
Base - emitter voltage	V _{BE}	V _{CE} = 10V, I _C = 5mA		0.62		
		V _{CE} = 1V, I _C = 1 A			1	
DC current gain	h _{FE}	V _{CE} = 10V, I _C = 5mA	50			
		V _{CE} = 1V, I _C = 500mA	85		375	
		V _{CE} = 1V, I _C = 1 A	60			
Collector capacitance	C _{ob}	V _{CB} = 5V, I _E = I _C =0, f=1MHz		38		pF
Transition frequency	f _T	V _{CE} = 5V, I _C = 10mA, f=100MHz	40			MHz

■ Typical Characteristics

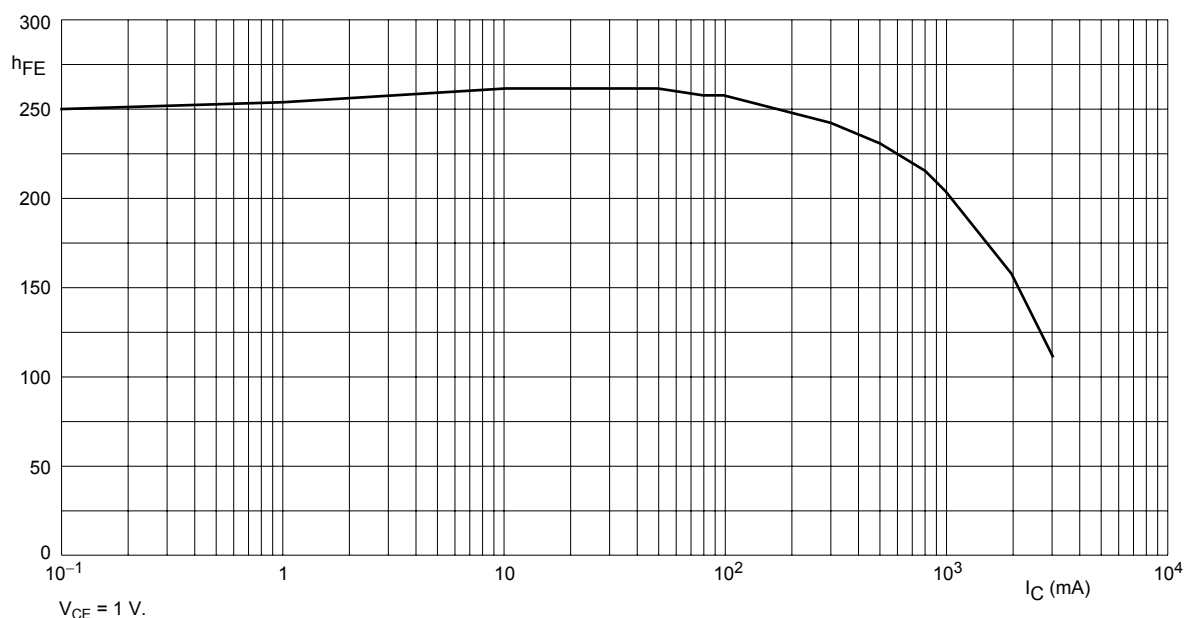


Fig.1 DC current gain; typical values.